## RERMCD1603 reliability plan for ATP UQFN3\*3 enhanced BOM - PCN 9610

#### **Reliability Evaluation Plan**

Mar 7<sup>th</sup>, 2016

MMS MCD Quality & Reliability Department



# PCN 9610- RERMCD1603 reliability plan for AMKOR ATP UQFN3\*3 COL 2 enhanced BOM

Context:

- Die Attach Film supplier stops its activity at NSCC location. STMicroelectronics will qualify new supplier location at Fujikura.
- Moreover, ST Microcontrollers Division takes the opportunity to improve package processability by changing the resin.

# RERMCD1603 STM8S/L TEST VEHICLES

Package line	Assembly Line	Package	Device (Partial RawLine Code)	Diffusion Process	Number of Lots
	UQFN3*3 COL	UQFN3*3 COL 20L	STM8S(E4*767)	F9GO1	1
UQFN			STM8L(E4*761)	F9GO2	1
			STM8L(E4*758)	F9GO2	1

## RERMCD 1602 - STM8S/L - UQFN RELIABILITY TRIALS

#### Package Reliability Trials :

(\*) tests performed after preconditioning

	Reliability Trial		Test Conditions	Pass Criteria	Unit per Lot	Lot qty
	PC	Pre Conditioning: Moisture Sensitivity Jedec Level 1 J-STD-020/ JESD22-A113	Bake (125°C / 24 hrs) Soak (85°C / 85% RH / 168 hrs) for level 1 Convection reflow: 3 passes with Jedec level 1	3 passes MSL1	308	1/ device
	AC or Uhast(*)	Autoclave JESD22 A102 or UnBiased Highly Accelerated Temperature and Humidity Stress JESD22 A118	121°C, 100% RH, 2 Atm 130°C, 85%RH, 2 Atm	96h	77	1/ device
	TC(*)	Thermal Cycling JESD22 A104	-50°C, +150°C Or equivalent -65°C +150°C	1000Cy 500Cy	77	1/ device
	WPT/WBS After TC	Wire Bond Pull- Mil Std883 method 2011 Wire Bond Shear AECQ100-001	3g min pull strengh 15g min bond shear	500Cy or 1000Cy upon test conditions	3 (30 wires) 3 (30 wires)	1/ device
	THB or THS(*)	Temperature Humidity Bias JESD22 A101 Or Temperature Humidity Storage JESD22 A110	85°C, 85% RH, bias 85°C, 85% RH, no bias	1000h 1000h	77	1/ device
	HTSL	High Temperature Storage Life	150°C- no bias	1000h	77	1/ device
	Construction analysis including Solderability, Physical dimensions	JESD 22B102 JESDB100/B108			15 10	1/ Front end technology
	ESD	ESD Charge Device Model ANSI/ESD STM5.3.1	500V depending on device datasheet	500V	3	1/ device

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